

DATA SHEET

BFQ262; BFQ262A NPN video transistors

Product specification
Supersedes data of November 1995
File under Discrete Semiconductors, SC05

1997 Oct 02

NPN video transistors

BFQ262; BFQ262A

FEATURES

- High breakdown voltages
- Low output capacitance
- Optimum temperature profile
- Good thermal stability
- Excellent reliability properties.

APPLICATIONS

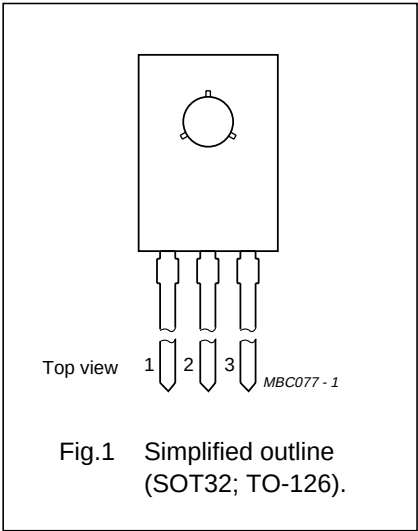
- Buffer/driver in high-resolution colour graphics monitors.

DESCRIPTION

NPN video transistor in a SOT32 (TO-126) plastic package.

PINNING

PIN	DESCRIPTION
1	emitter
2	collector
3	base



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{CBO}	collector-base voltage BFQ262 BFQ262A	open emitter	—	—	100	V
			—	—	115	V
V _{CER}	collector-emitter voltage BFQ262 BFQ262A	R _{BE} = 100 Ω	—	—	95	V
			—	—	110	V
I _C	collector current (DC)		—	—	400	mA
P _{tot}	total power dissipation	T _s ≤ 85 °C; note 1	—	—	5	W
h _{FE}	DC current gain BFQ262 BFQ262A	I _C = 100 mA; V _{CE} = 10 V; T _{amb} = 25 °C	50	60	—	
			20	35	—	
f _T	transition frequency BFQ262 BFQ262A	I _C = 100 mA; V _{CE} = 10 V; f = 100 MHz; T _{amb} = 25 °C	1	1.4	—	GHz
			0.8	1.2	—	GHz

Note

1. T_s is the temperature at the soldering point of the collector pin.

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
	BFQ262		–	100	V
	BFQ262A		–	115	V
V _{CEO}	collector-emitter voltage	open base			
	BFQ262		–	65	V
	BFQ262A		–	95	V
V _{CER}	collector-emitter voltage	R _{BE} = 100 Ω			
	BFQ262		–	95	V
	BFQ262A		–	110	V
V _{EBO}	emitter-base voltage	open collector	–	3	V
I _C	collector current (DC)		–	400	mA
P _{tot}	total power dissipation	T _S $\leq$ 85 $^{\circ}$ C; note 1; see Fig.3	–	5	W
T _{stg}	storage temperature		–65	+150	$^{\circ}$ C
T _j	junction temperature		–	175	$^{\circ}$ C

Note

1. T_S is the temperature at the soldering point of the collector pin.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-s}	thermal resistance from junction to soldering point	T _S $\leq$ 85 $^{\circ}$ C; note 1	18	K/W

Note

1. T_S is the temperature at the soldering point of the collector pin.

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CHARACTERISTICS

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)CBO}$	collector-base breakdown voltage BFQ262 BFQ262A	$I_C = 0.1\text{ mA}; I_E = 0$	100	–	–	V
			115	–	–	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage BFQ262 BFQ262A	$I_C = 10\text{ mA}; I_B = 0$	65	–	–	V
			95	–	–	V
$V_{(BR)CER}$	collector-emitter breakdown voltage BFQ262 BFQ262A	$I_C = 10\text{ mA}; R_{BE} = 100\text{ }\Omega$	95	–	–	V
			110	–	–	V
$V_{(BR)EBO}$	emitter-base breakdown voltage	$I_E = 0.1\text{ mA}; I_C = 0$	3	–	–	V
I_{CES}	collector-emitter cut-off current	$I_B = 0; V_{CE} = 50\text{ V}$	–	–	100	μA
I_{CBO}	collector-base cut-off current	$I_E = 0; V_{CB} = 50\text{ V}$	–	–	20	μA
h_{FE}	DC current gain BFQ262 BFQ262A	$I_C = 100\text{ mA}; V_{CE} = 10\text{ V};$ $T_{amb} = 25\text{ }^{\circ}\text{C};$ see Fig.4	50	60	–	
			20	35	–	
f_T	transition frequency BFQ262 BFQ262A	$I_C = 100\text{ mA}; V_{CE} = 10\text{ V};$ $f = 100\text{ MHz}; T_{amb} = 25\text{ }^{\circ}\text{C};$ see Fig.6	1	1.4	–	GHz
			0.8	1.2	–	GHz
C_{cb}	collector-base capacitance	$I_C = I_E = 0; V_{CB} = 10\text{ V};$ $f = 1\text{ MHz}; T_{amb} = 25\text{ }^{\circ}\text{C};$ see Fig.5	–	2	–	pF
C_c	collector capacitance	$I_E = I_C = 0; V_{CB} = 10\text{ V};$ $f = 1\text{ MHz}$	–	3.5	–	pF

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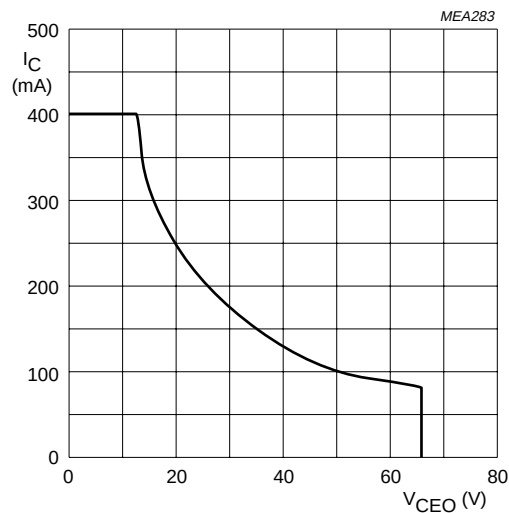


Fig.2 DC SOAR.

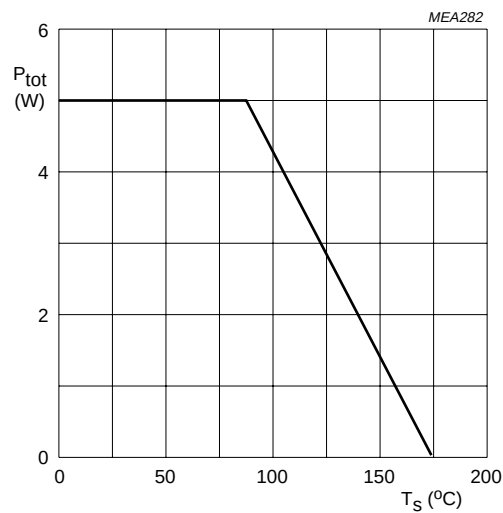
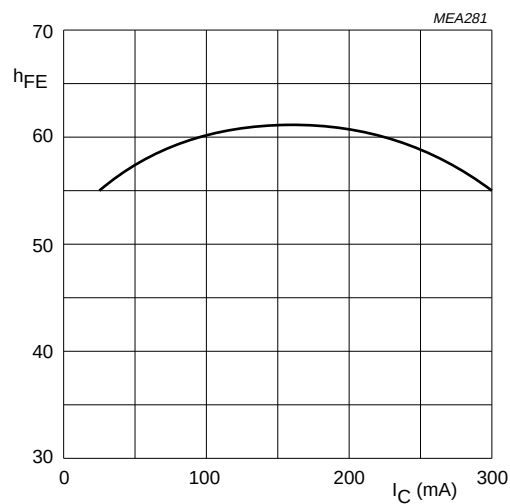
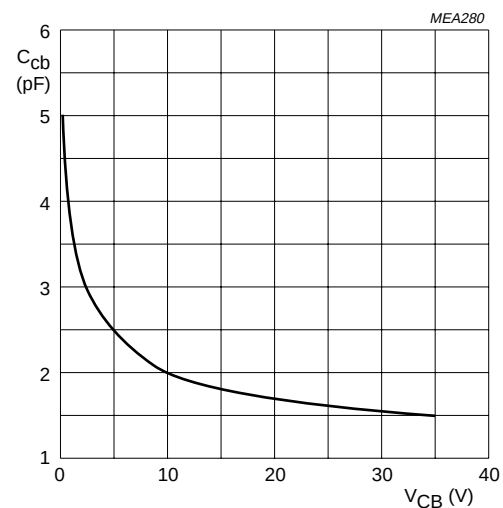


Fig.3 Power derating curve.



$V_{CE} = 10$ V; $T_{amb} = 25$ $^{\circ}\text{C}$.

Fig.4 DC current gain as a function of collector current; typical values.

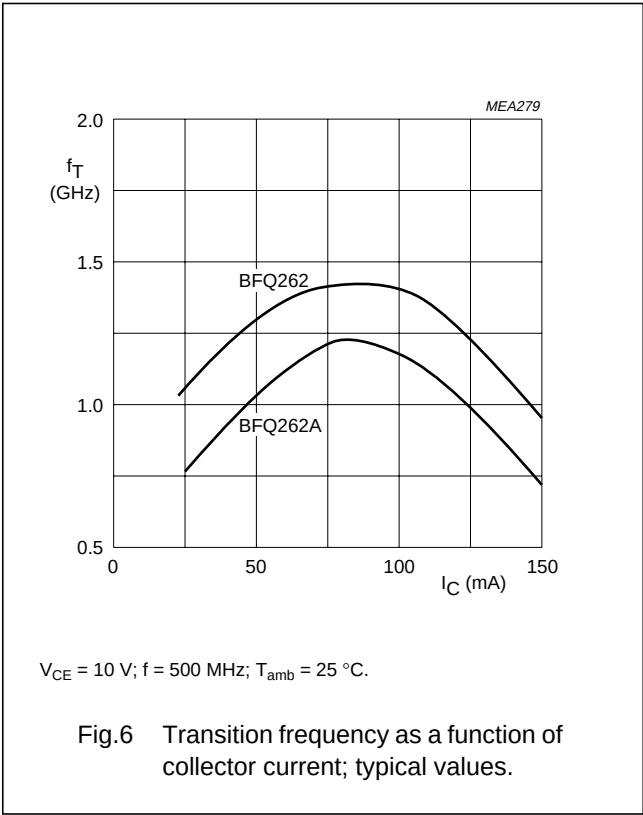


$f = 1$ MHz; $T_{amb} = 25$ $^{\circ}\text{C}$.

Fig.5 Collector-base capacitance as a function of collector-base voltage; typical values.

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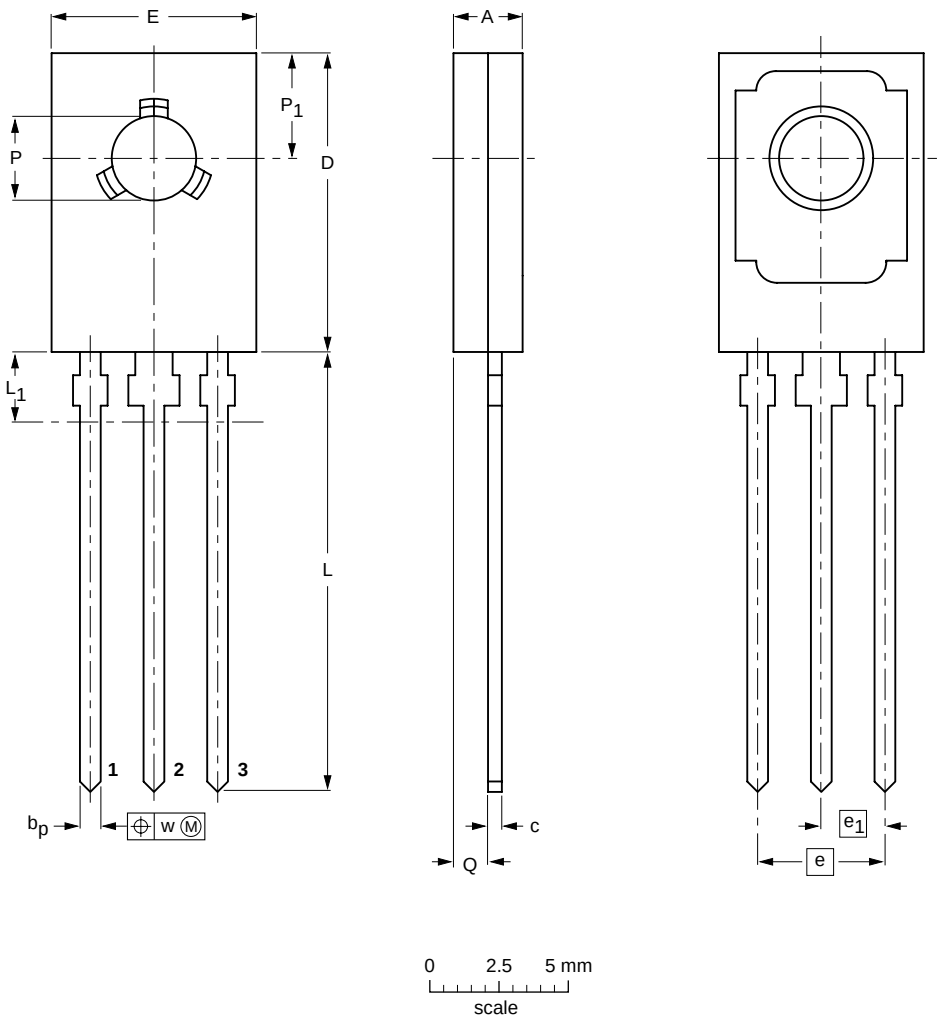


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PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; mountable to heatsink, 1 mounting hole; 3 leads SOT32

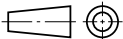


DIMENSIONS (mm are the original dimensions)

UNIT	A	b _p	c	D	E	e	e ₁	L	L ₁ ⁽¹⁾ max	Q	P	P ₁	w
mm	2.7 2.3	0.88 0.65	0.60 0.45	11.1 10.5	7.8 7.2	4.58	2.29	16.5 15.3	2.54	1.5 0.9	3.2 3.0	3.9 3.6	0.254

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT32		TO-126				97-03-04

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DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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NOTES

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NOTES

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